Multiscale Materials Modeling

Chuin-Shan David Chen

Professor, F. IACM, Department of Civil Engineering National Taiwan University, Email: dchen@ntu.edu.tw

Computer Simulation and Physical Testing of Complex Fracturing Processes Symposium in honor of Prof. Anthony R. Ingraffea on his retirement September 27, 2014

Fatigue and fracture in metal: from cracks in the rivet holes to voids in grains to dislocation and atomistic fracture



DISLOCATIONS AND MECHANICAL PROPERTY

David (C-S) Chen

 Large-scale atomistic simulation opens a new way to study mechanics of materials.

> Gold-coated microcantilever

 $t = 0.6 \, \mu m$





Nano-twinned Metal Nature (2010)

~ 10^9 atoms

Nanomedicine targets cancer, Scientific American, Feb 2009 200,000 x 40,000 x 600nm ~ 10¹⁴ atoms

 $w = 40 \ \mu m$

= 200 µm

• (Key features) mechanisms and properties are emerged directly from fundamental evolution of atoms.

Sensing

CANTILEVERS

Sample DNA

Probe DNA

ELASTIC DEFORMATION



David (C-S) Chen

PLASTIC DEFORMATION (SHEAR and SLIP)



Dislocation and Plasticity

 Glide of dislocations results in slip, the most common manifestation of plastic deformation in crystalline solids.



David (C-S) Chen

Atomistic Simulation Environment

- Specimen samples

 Contains ~10⁸ atoms.
- Empirical interatomic potential: embedded atom method (EAM)
 – FCC metals (Baskes 1992).
- Quasi-static, conjugate gradient (CG) minimization.
- LAMMPS: an open source molecular dynamics program.



Dislocation Extraction From Burgers Circuit



David (C-S) Chen

Nanoindentation: Dislocation Evolution



David (C-S) Chen

Dislocations Glide When $\tau > \tau_c$



David (C-S) Chen

Cross Slip of Screw Dislocations



David (C-S) Chen

Lomer Lock Blocks Dislocations



Indentation Size Effect (Smaller is Stronger)



Hardness increases when indenter radius decreases.

David (C-S) Chen

Indentation Size Effect: The Quest

- (Imagine) We push atoms into the underneath material.
- Atoms become extra planes of atoms (dislocations) in the original lattice.
- These dislocations are called geometrically necessary dislocations (GNDs).
- GNDs are believed to block other mobile dislocations thus contribute to hardening.
- The smaller indents, the higher density of GNDs, and thus stronger.





Repulsive Force Field for Indenters

$$F_i = \mathcal{E}(r - r_i)^2$$
 (Plimpton 1995)

- Spherical Indenter
 - Smooth transition from elastic to elastic-plastic contact
- Berkovich Indenter
 - Routinely used in nanoindentation tests





Hardness Calculation



Hardness vs. Dislocation Evolution



Materials Strength ≡ restricted dislocation motion.

Hardness - Spherical



David (C-S) Chen

Quantify Density of Geometrically Necessary Dislocations (ρ_g)





Hardness (Property) and GNDs (Mechanism)



0.01 0.005

Indentation depth, Å Civil Engineering, NTU

David (C-S) Chen

VOID NUCLEATION AND GROWTH

David (C-S) Chen

Ultra High Temperature Ceramics



David (C-S) Chen

ZrB₂-SiC Ceramic Composites



Modeling Intergranular Fracture





Micromechanics Model: Simple Grain

- Constitutive model of ceramic grain
 - Superposition of strain rate

$$\dot{\mathcal{E}}_{ij} = \dot{\mathcal{E}}_{ij}^e + \dot{\mathcal{E}}_{ij}^{cr}$$

$$\sigma_{ij}^{(m+1)} = \mathbf{D} \left(\varepsilon_{ij}^{(m+1)} - \varepsilon_{ij}^{cr(m+1)} \right)$$
$$\mathbf{D} = \frac{E}{(1+\nu)(1-2\nu)} \begin{bmatrix} 1-\nu & \nu & 0 \\ \nu & 1-\nu & 0 \\ 0 & 0 & 1-2\nu \end{bmatrix}$$

 Power law creep rate for a ceramic grain



Micromechanics Model: Grain Boundary

• Smeared out cohesive model for grain boundary





a: cavity radiusb: half cavity spacingV: cavity volume

$$V = \frac{4}{3}\pi a^{3}h(\psi)$$

and
$$h(\psi) = \frac{\left[(1 + \cos\psi)^{-1} - \frac{1}{2}\cos\psi\right]}{\sin\psi}$$

Grain separation in normal direction can be expressed by

$$u_n = \frac{V}{\pi b^2}$$

Micromechanics Model: Grain Boundary

Normal separation rate

$$\dot{u}_n = \frac{\dot{V}}{\pi b^2} - \frac{2V\dot{b}}{\pi b^3}$$



- Three ingredients in normal separation rate at grain boundary
 - Cavity nucleation
 - Cavity growth enabled by atom diffusion
 - Cavity growth enabled by creep

Cavity Nucleation



 Cavity density of undefomed grain boundary

$$N = \frac{1}{\pi b^2}$$

• The change rate of void spacing

$$\frac{\dot{b}}{b} = \frac{1}{2}(\dot{\varepsilon}_{I} + \dot{\varepsilon}_{II}) - \frac{1}{2}\frac{\dot{N}}{N}$$

where $\dot{\mathcal{E}}_{I}$ and $\dot{\mathcal{E}}_{II}$ are the principal logarithmic strain rates at grain boundary

Cavity Nucleation Rule

Cavity density rate

$$\dot{N} = F_n \left(\frac{\sigma_n}{\Sigma_0}\right)^2 \dot{\varepsilon}_e^C$$

 F_n is material parameter, σ_n is normal traction, Σ_0 is a normalized factor, and $\dot{\varepsilon}_e^C$ is the effective strain which is the average value of adjacent grains.



Cavity Growth

Cavity growth from diffusion • Cavity growth from creep ullet



$$\dot{V}_1 = 4\pi D \frac{\sigma_n}{\ln(\frac{1}{f}) - \frac{1}{2}(3 - f)(1 - f)}$$

where

$$f = \max\left\{ \left(\frac{a}{b}\right)^2, \left(\frac{a}{a+1.5L}\right)^2 \right\}$$

and
$$L = \left[D \frac{\sigma_e}{\dot{\varepsilon}_e^c} \right]^{\frac{1}{3}}$$



$$\dot{V}_{2} = \begin{cases} \pm 2\pi \dot{\varepsilon}_{e}^{c} a^{3} h(\psi) [\alpha_{n} \left| \frac{\sigma_{m}}{\sigma_{e}} \right| + \beta_{n}]^{n}, & \text{for } \pm \frac{\sigma_{m}}{\sigma_{e}} > 1 \\ 2\pi \dot{\varepsilon}_{e}^{c} a^{3} h(\psi) [\alpha_{n} + \beta_{n}]^{n} \frac{\sigma_{m}}{\sigma_{e}}, & \text{for } \left| \frac{\sigma_{m}}{\sigma_{e}} \right| < 1 \end{cases}$$

where σ_e and σ_m are the average effective stress and mean stress from adjacent grains; and

$$\alpha_n = \frac{3}{2n} \quad \beta_n = \frac{(n-1)(n+0.4319)}{n^2}$$

Civil Engineering, NTU

David (C-S) Chen





Intergranular Fracture: Experimental Observation

Micrograph at the tension side after creep test at 1700°C

- SiC acts as microstructure anchors and some lead to cavitation but not all.
- SiC remains near constant shape (relatively high rigidity)
- Cavitation is only observed at high temperature region (above 1500°C)
- About 5% cavitation is found at ZrB₂-SiC grain boundary and the rotation angle is less than 3°

Polycrystalline Model

Comparison of Strain Rate

- Simulation results show a significant variation when cavitation nucleation was assigned.
- Simulation with nucleation allowed at ZrB₂-SiC interface show a great agreement with experiment data

Grain Rotation

scale 100 times. Nucleation occurs at ZS grain boundary as softening

10 11 12 ID 3 5 8 9 7 Angle 0.008 0.011 0.004 0.015 0.004 0.007 0.035 0.008 0.030 0.004 0.003 0.014 (b) With nucleation @ ZS grain 8 9 10 11 ID 3 5 6 7 0.12 Angle 0.02 0.17 0.37 0.09 2.14 1.37 2.67 0.13 0.22 0.01 0.04

(a) Without nucleation

David (C-S) Chen

Civil Engineering, NTU

12

Tensile Stress Contour

without nucleation

nucleation at ZrB₂-SiC

Severe stress concentration at ZrB₂-SiC grain boundary when nucleation is not allowed.

Fatigue and fracture in metal: from cracks in the rivet holes to voids in grains to dislocation and atomistic fracture

"Crystals are like people, it is the defects in them which tend to make them interesting!" - Colin Humphreys

From Tony, 1991.12

DAVID (Chuin-Shan) CHEN !!!

THIS IS A PUBLIC THANK YOU FOR BEING AN **OUTSTANDING TA** IN CE 673

STUDENTS AND PROFESSOR ALIKE APPLAUD YOU FOR YOUR KNOWLEDGE, CARING, AND ACCESSIBILITY.

Driven and Determine

Achieving one's dream in the most Gracious Manner

Braving all Obstacles with Confidence and

Emerged as a Glorious Winner

